Abstracts

High-Frequency Transistor Evaluation by Three-Port Scattering Parameters

A.P. Anderson. "High-Frequency Transistor Evaluation by Three-Port Scattering Parameters." 1967 Transactions on Microwave Theory and Techniques 15.4 (Apr. 1967 [T-MTT]): 263-265.

Semiconductor technology has developed sufficiently for transistors to retain useful properties up into the microwave region. One GHz is the approximate lower-frequency limit of this region, although a preferable concept might be to consider a transistor in microwave terms when the encapsulation design and associated jig or holder impedances have significant effect. One such effect is the reduction of measurement accuracy for admittance parameters, due to the increasing difficulty of specifying reference planes. Frequency characteristics of the jig and its interaction with the device must also be considered.

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